



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOT-23 封装半导体晶体管/SOT-23 Plastic-Encapsulate Transistors

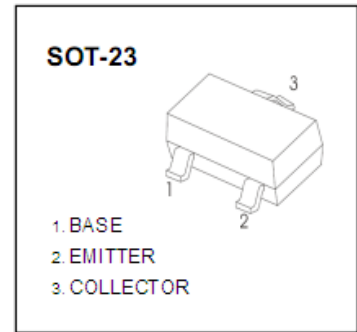
2SC2712 (NPN)

特点/Features :

噪声低，放大线性好;

用途/Applications :

用于一般放大。



极限参数/Absolute maximum ratings(Ta=25°C)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	V_{CB0}	60	V
集电极-发射极电压/Collector-Emitter Voltage	V_{CE0}	50	V
发射极-基极电压/Emitter-Base Voltage	V_{EB0}	5	V
集电极连续电流/Collector Current Continuous	I_C	0.15	A
集电极耗散功率/Collector Power Dissipation	P_C	0.15	W
结温/Junction Temperature	T_j	150	°C
储存温度/Storage Temperature	T_{stg}	-55~150	°C

电性能参数/Electrical characteristics (Ta=25°C)

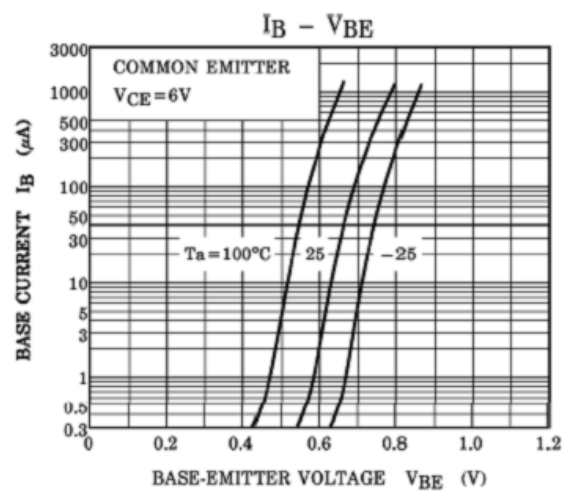
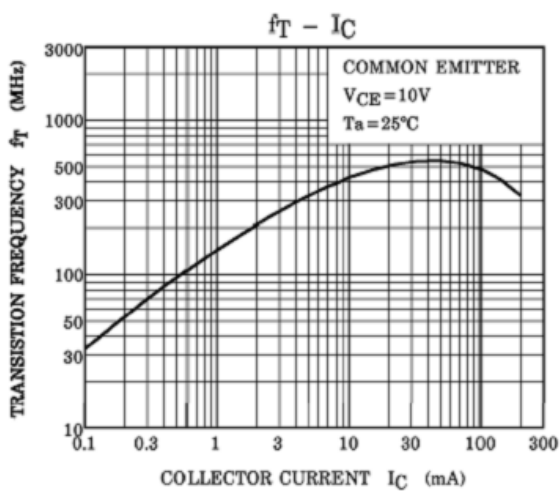
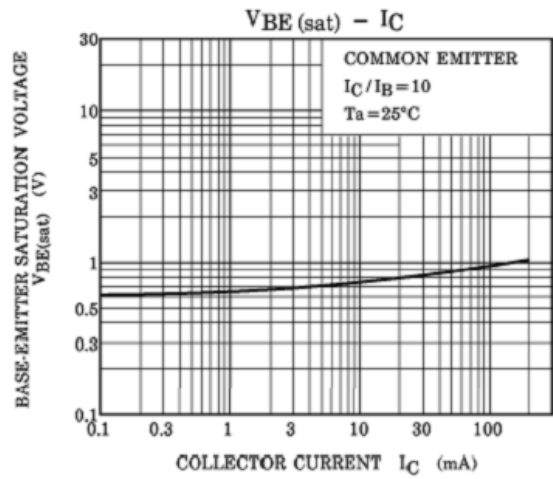
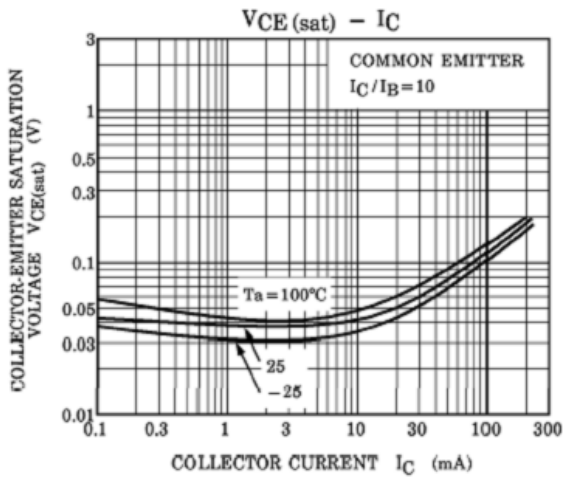
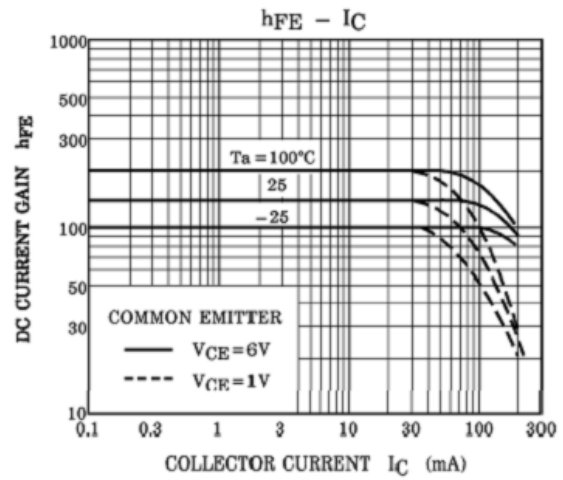
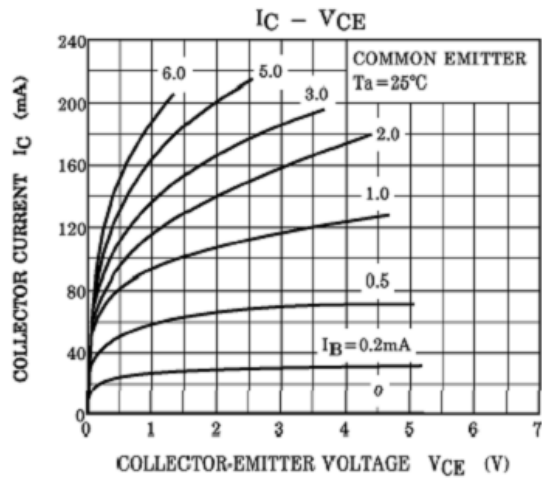
参数	符号	测试条件	最小值	典型值	最大值	单位
集电极-基极击穿电压	$V_{BR(CB0)}$	$I_C=100 \mu A, I_E=0$	60			V
集电极-发射极击穿电压	$V_{BR(CE0)}$	$I_C=1mA, I_B=0$	50			V
发射极-基极击穿电压	$V_{BR(EB0)}$	$I_E=100 \mu A, I_C=0$	5			V
集电极截止电流	I_{CB0}	$V_{CB}=60V, I_E=0$			0.1	μA
发射极截止电流	I_{EB0}	$V_{EB}=5V, I_C=0$			0.1	μA
直流电流增益	h_{FE}	$V_{CE}=6V, I_C=2mA$	70		700	
集电极-发射极饱和压降	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$		0.1	0.25	V
特征频率	f_T	$V_{CE}=10V, I_C=1mA$	80			MHz
输出电容	C_{ob}	$V_{CB}=10 V, I_E=0, f=1MHz$		2.0	3.5	pF
噪声系数	NF	$V_{CE}=6V, I_C=0.1mA, f=1kHz,$ $R_g=10K \Omega$		1.0	10	dB

Marking And h_{FE} 分档/Classification of h_{FE}

档位/Rank	0	Y	GR	BL
范围/Range	70~140	120~240	200~400	350~700
印章/Marking	L0	LY	LG	LL



典型特性曲线图/Typical Characteristics





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